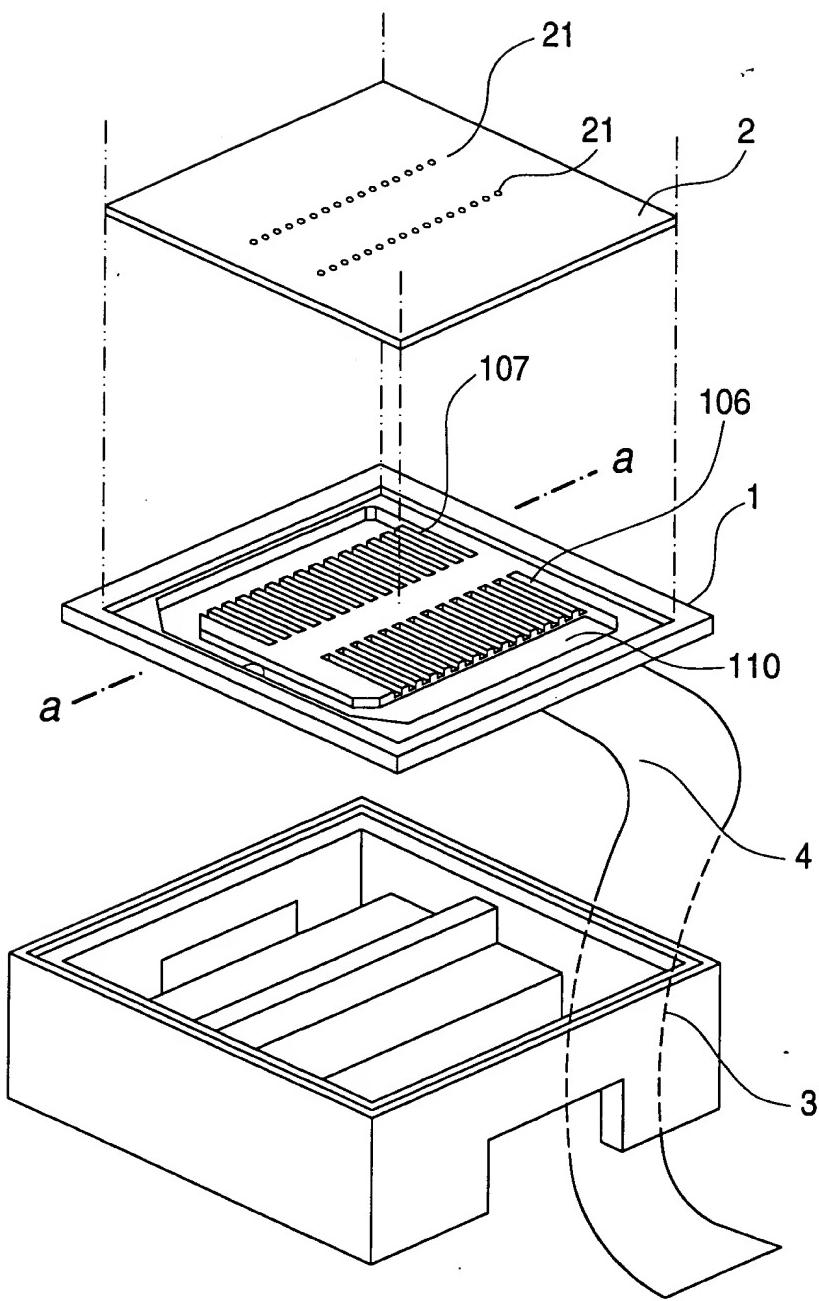


89/599,440

1/17

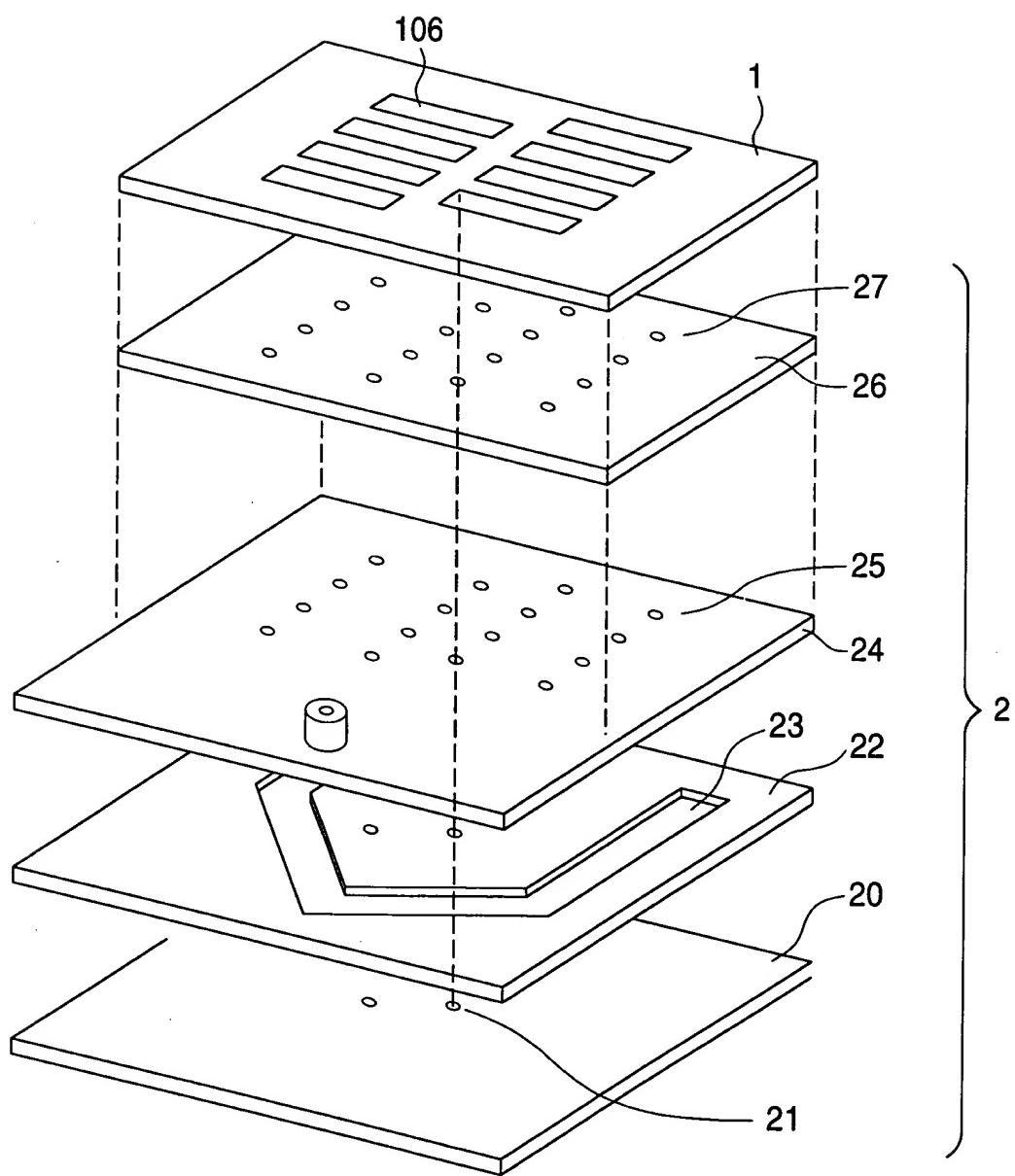
FIG. 1



09/598,840

2/17

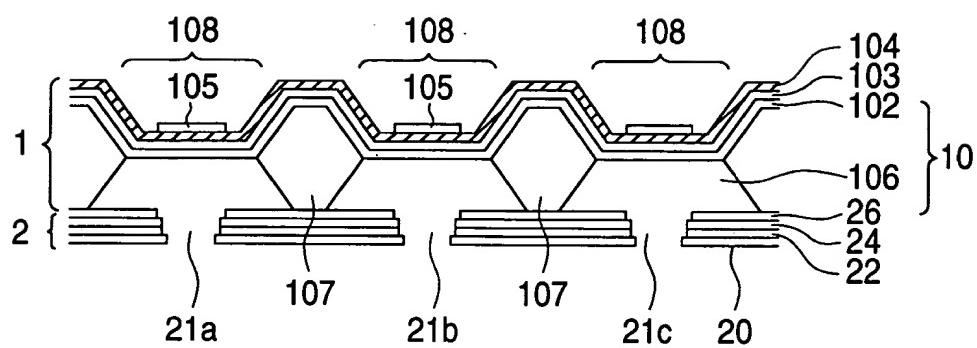
FIG. 2



89/599,440

3/17

FIG. 3



09/599,440

4/17

FIG. 4A

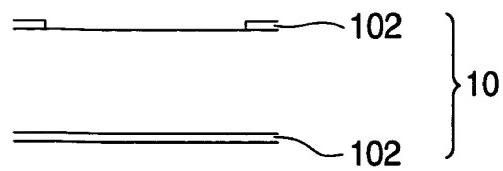


FIG. 4B

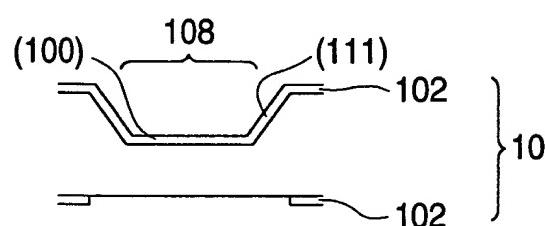


FIG. 4C

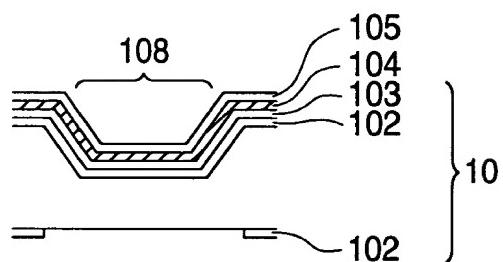


FIG. 4D

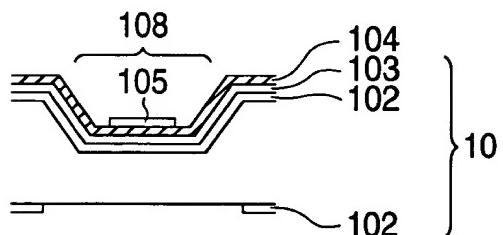
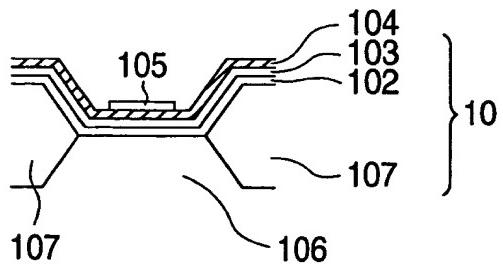


FIG. 4E



69/599,449

5/17

FIG. 5

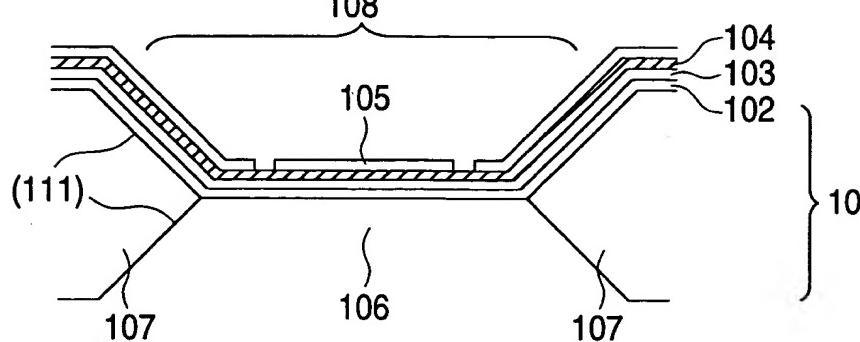


FIG. 6

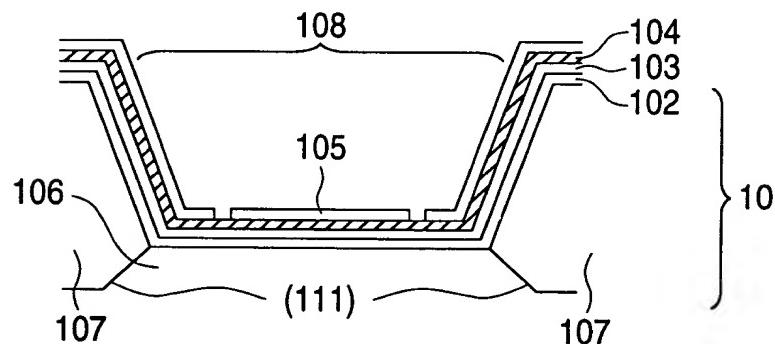
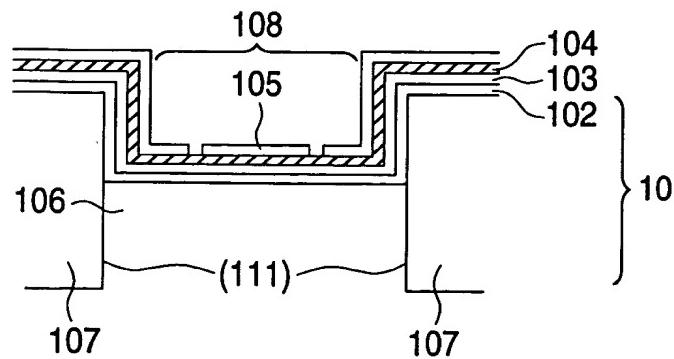


FIG. 7



09/599440

6/17

FIG. 8

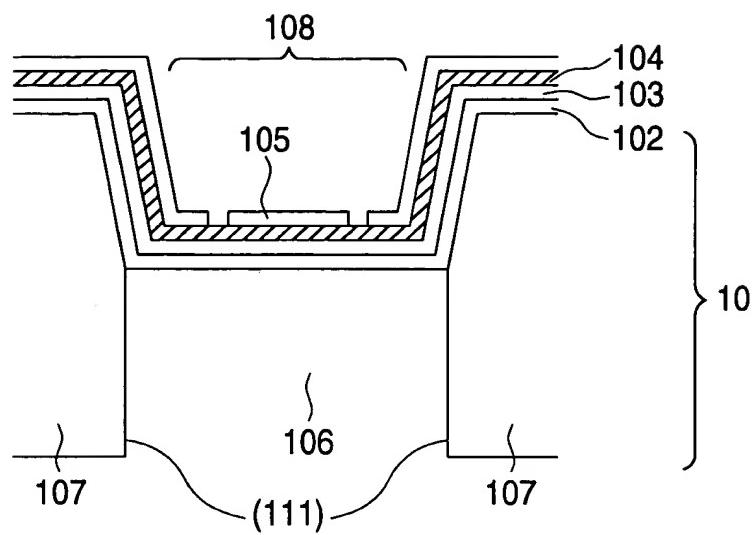
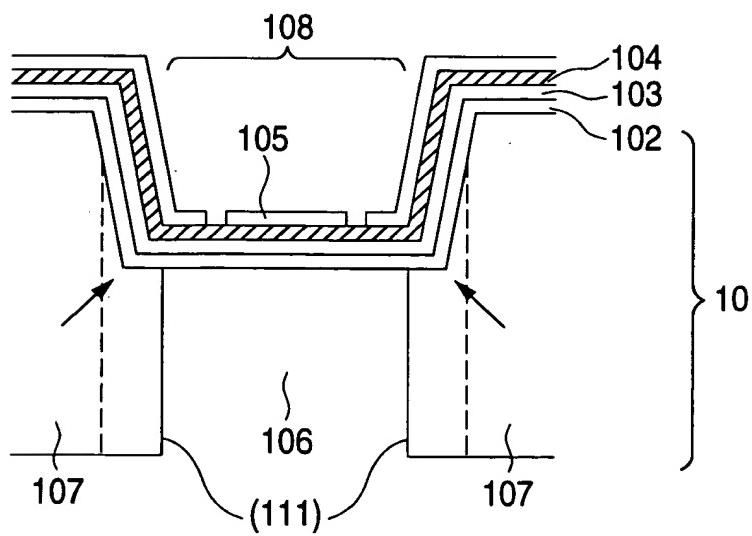


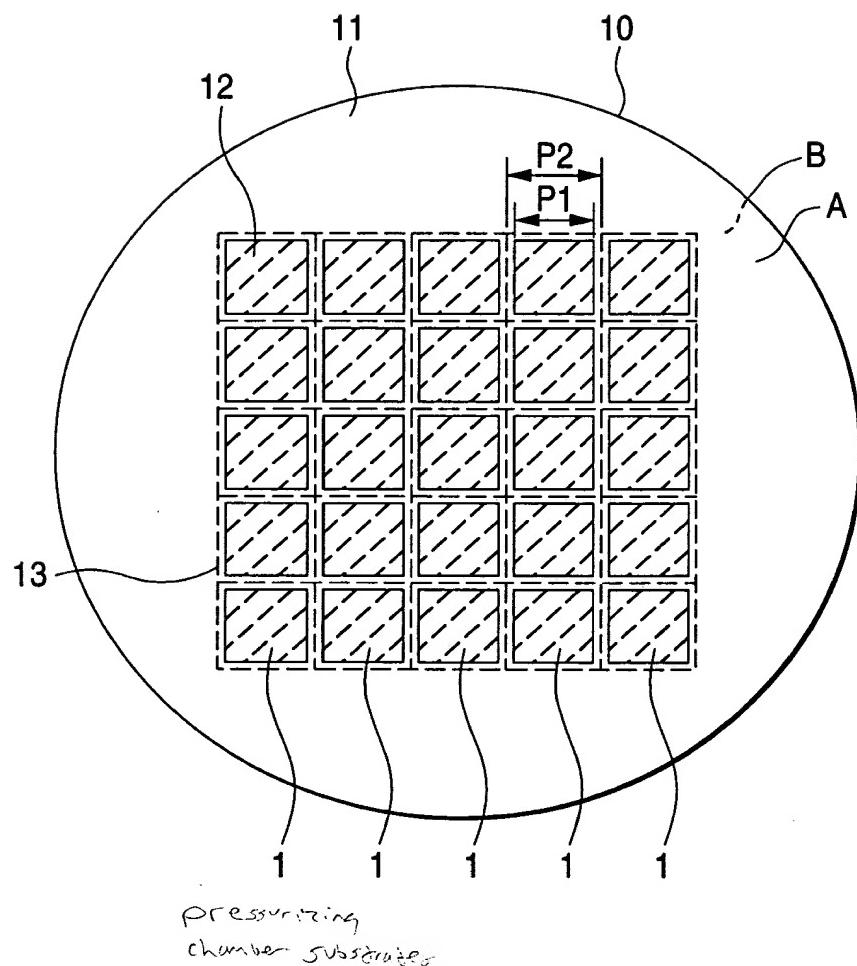
FIG. 9



09/599440

7/17

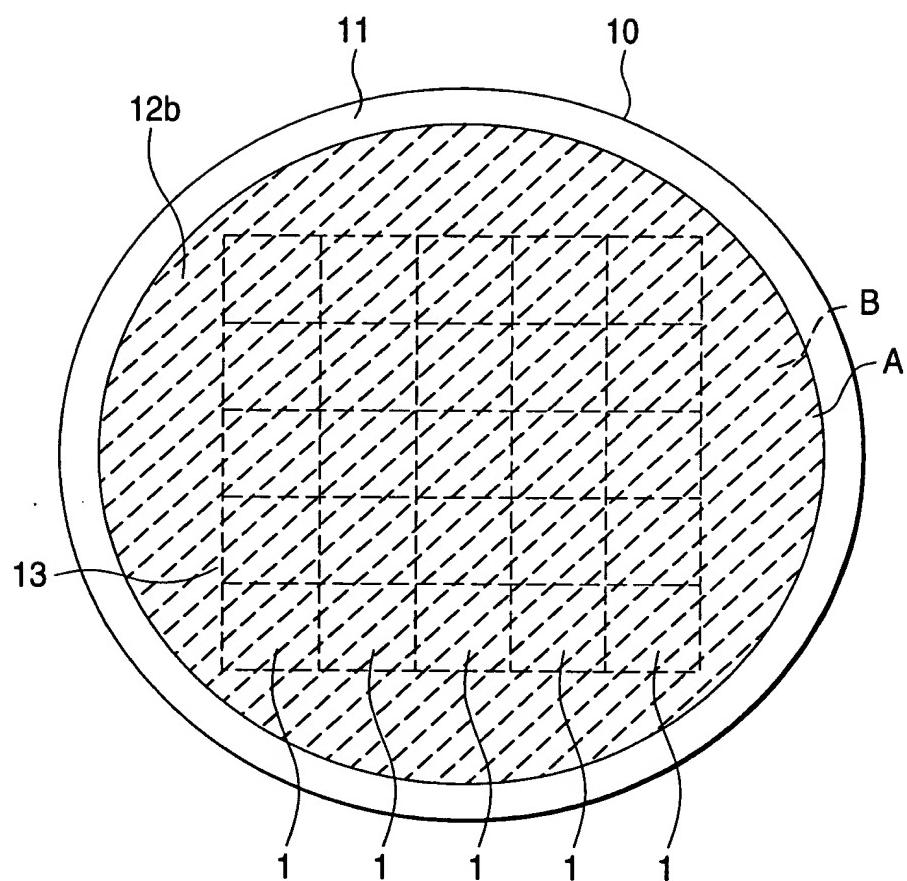
FIG. 10



09/599480

8/17

FIG. 11



69/599440

9/17

FIG. 12A

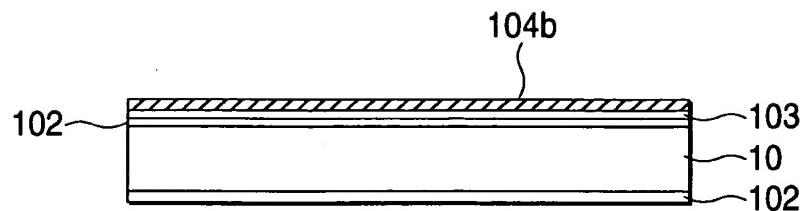


FIG. 12B

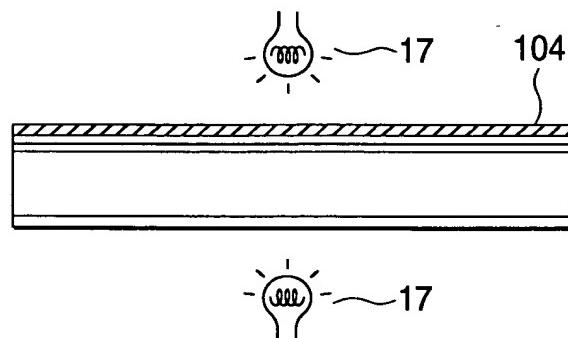


FIG. 12C

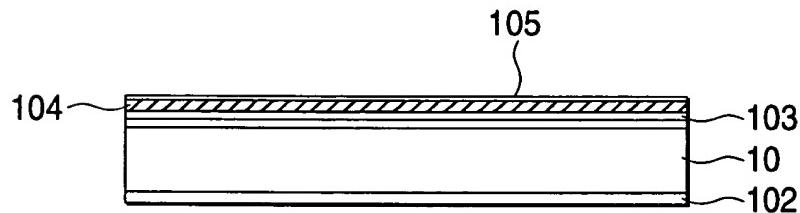


FIG. 12D

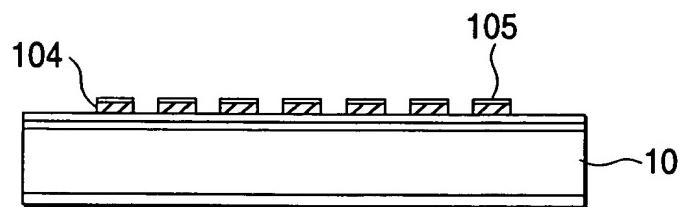
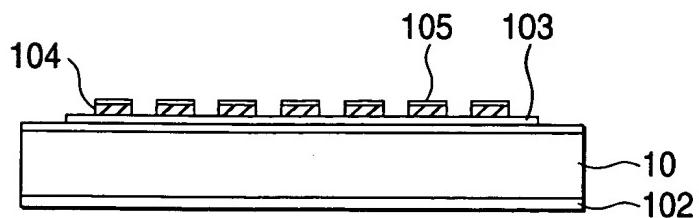


FIG. 12E



09/599444

10/17

FIG. 13F

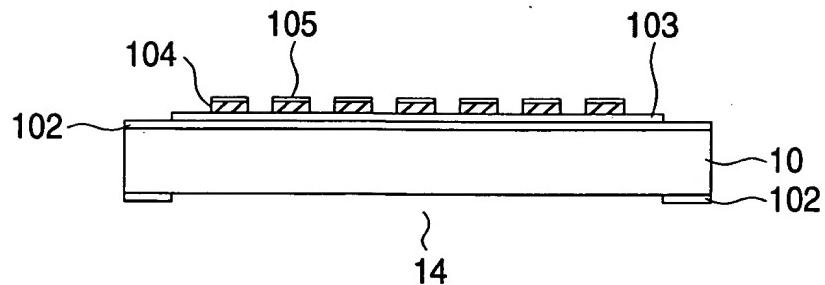


FIG. 13G

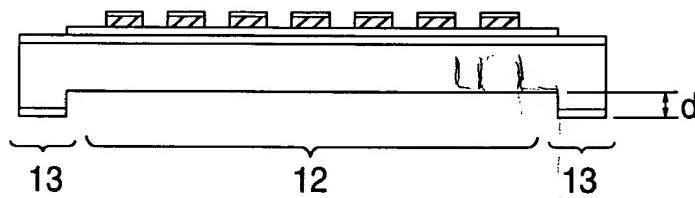


FIG. 13H

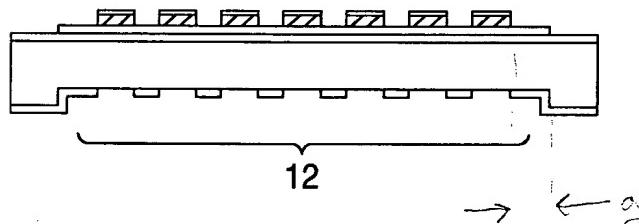


FIG. 13I

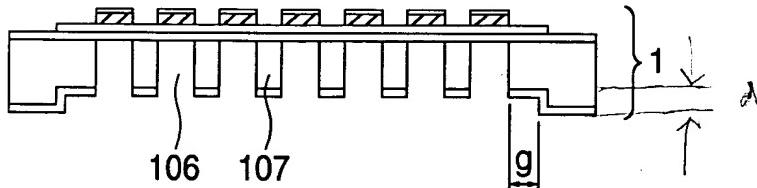
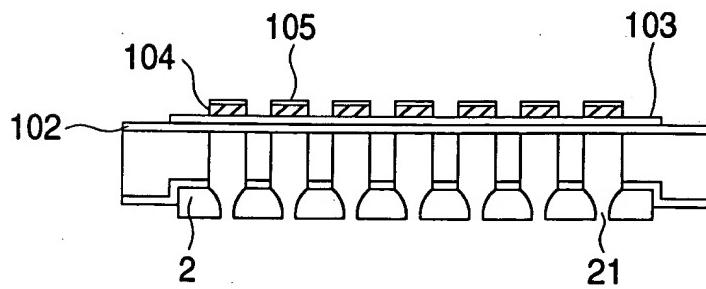


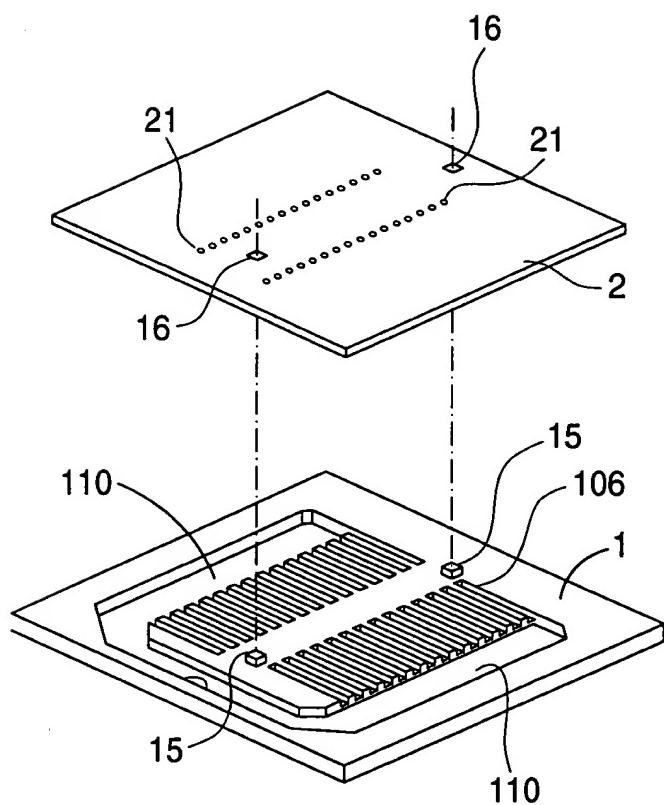
FIG. 13J



09/598440

11/17

FIG. 14



09/599440

12/17

FIG. 15F

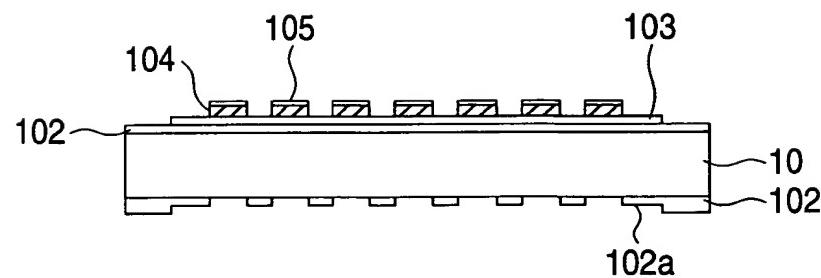


FIG. 15G

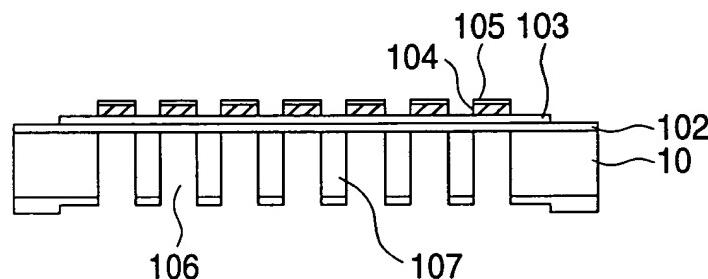


FIG. 15H

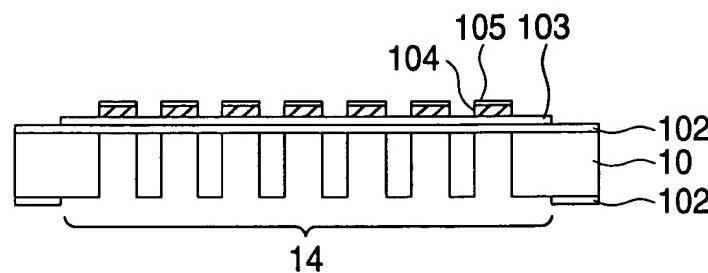
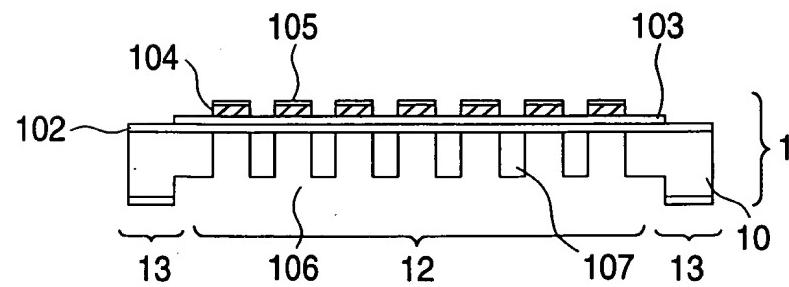


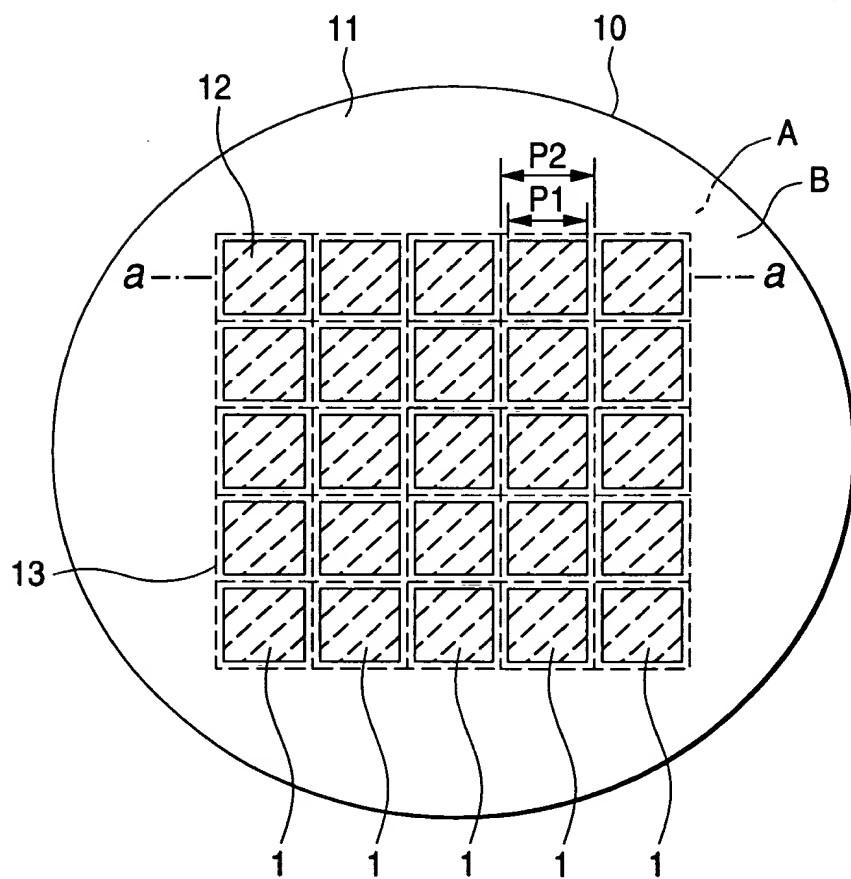
FIG. 15I



09/599940

13/17

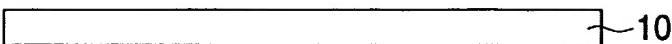
FIG. 16



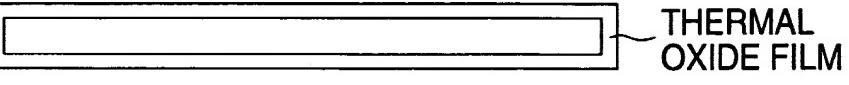
09/599446

14/17

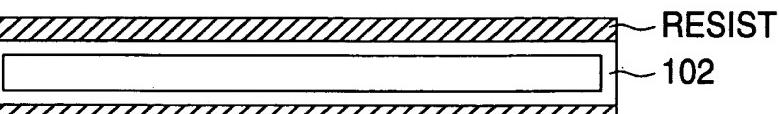
**FIG. 17A**

WATER CLEANING 

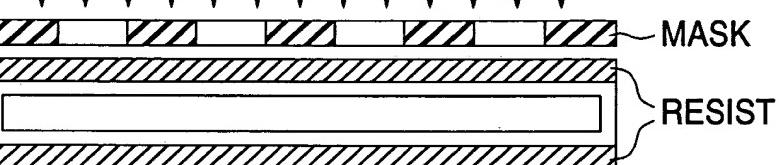
**FIG. 17B**

LAYER-TO-BE-PROCESSED FORMATION 

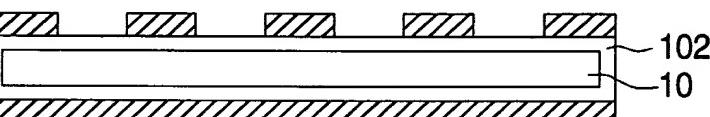
**FIG. 17C**

RESIST APPLICATION 

**FIG. 17D**

EXPOSURE 

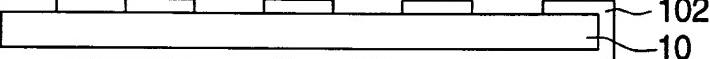
**FIG. 17E**

DEVELOPMENT 

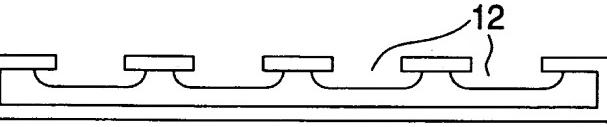
**FIG. 17F**

ETCHING 

**FIG. 17G**

RESIST REMOVAL 

**FIG. 17H**

SILICON ETCHING 

**FIG. 17I**

THERMAL OXIDE FILM ETCHING 

**FIG. 17J**

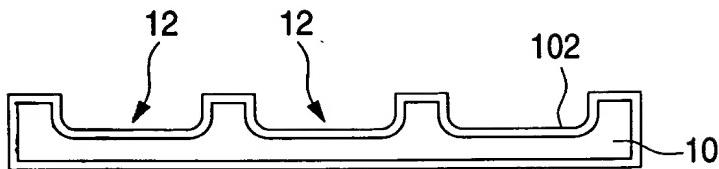
FILM-TO-BE-PROCESSED FORMATION 

09/599440

15/17

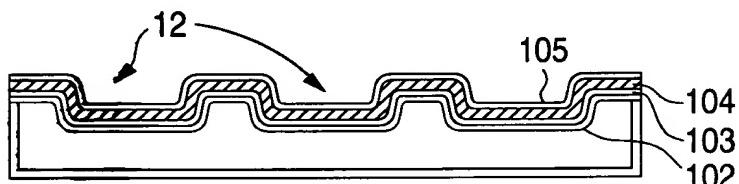
**FIG. 18A**

OSCILLATING PLACE  
FILM FORMATION



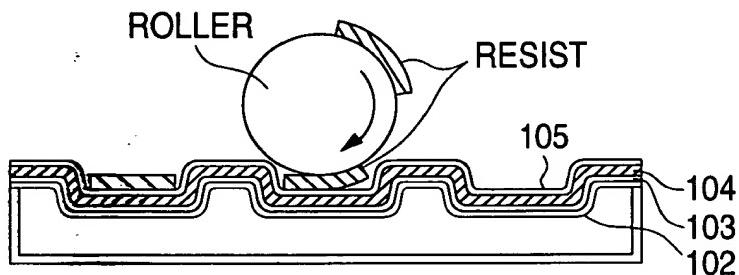
**FIG. 18B**

PIEZOELECTRIC  
SUBSTANCE FORMATION



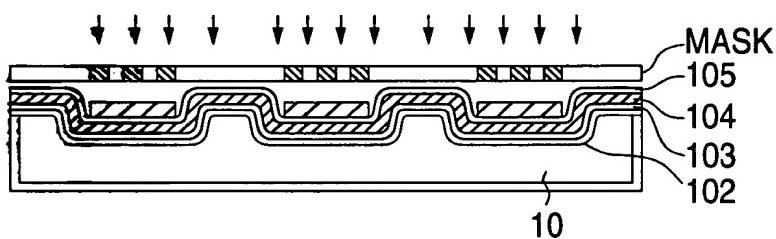
**FIG. 18C**

RESIST FORMATION



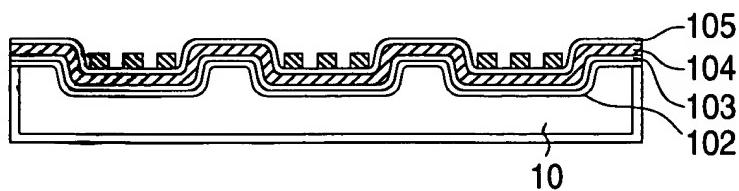
**FIG. 18D**

MASK EXPOSURE



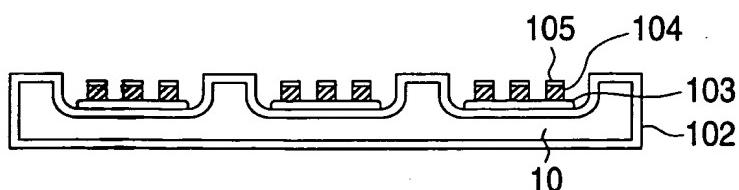
**FIG. 18E**

DEVELOPMENT



**FIG. 18F**

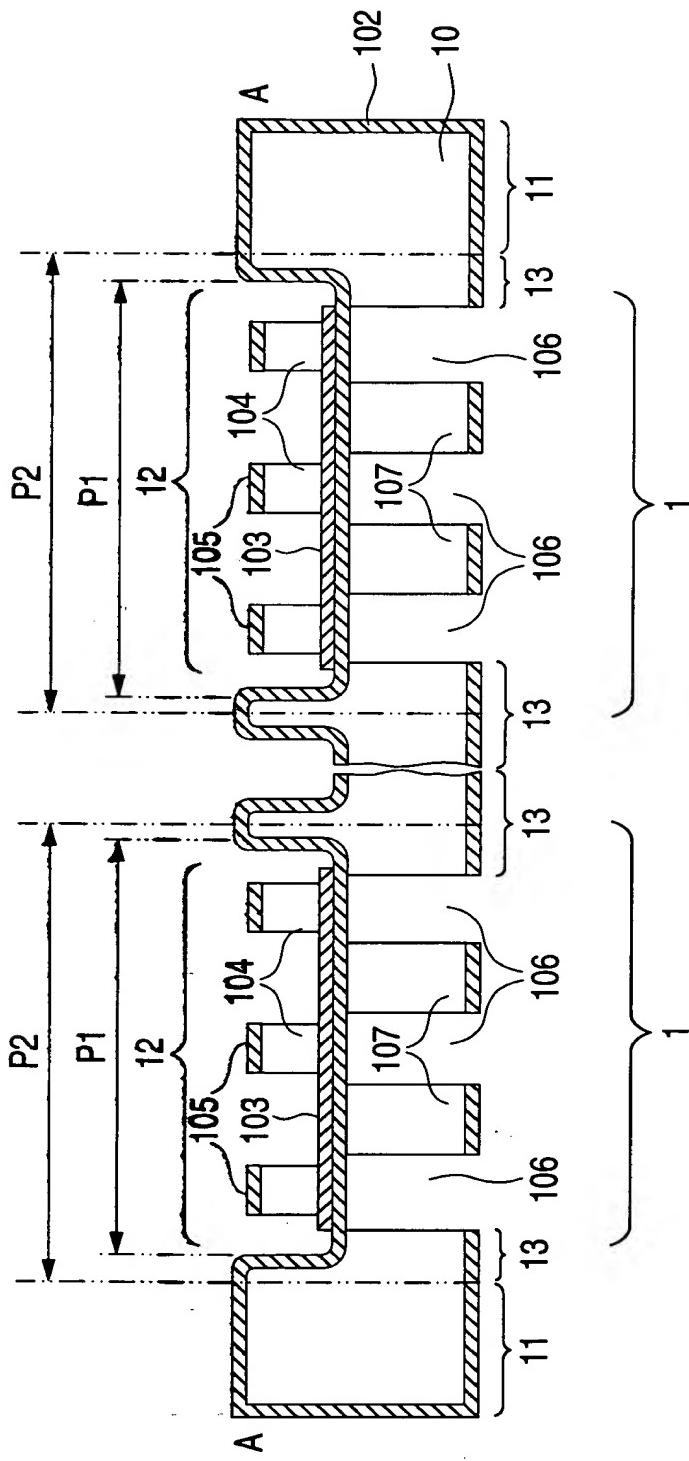
ETCHING



09/599449

16/17

FIG. 19



69/599446

17/17

FIG. 20

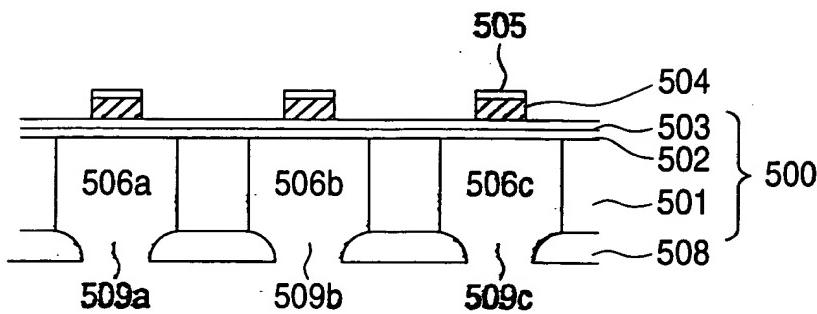


FIG. 21

